



# Low-Voltage Single SPDT MICRO FOOT® Analog Switch

### **DESCRIPTION**

The DG3000 is a single-pole/double-throw monolithic CMOS analog switch designed for high performance switching of analog signals. Combining low power, high speed  $(t_{ON}: 24 \text{ ns}, t_{OFF}: 9 \text{ ns})$ , low on-resistance  $(R_{DS(on)}: 1.4 \Omega)$ and small physical size (MICRO FOOT, 6-bump), the DG3000 is ideal for portable and battery powered applications requiring high performance and efficient use of board space.

The DG3000 is built on Vishay Siliconix's low voltage JI2 process. An epitaxial layer prevents latchup. Break-before make is guaranteed for DG3000.

Each switch conducts equally well in both directions when on, and blocks up to the power supply level when off.

As a committed partner to the community and the environment, Vishay Siliconix manufactures this product with the lead (Pb)-free device terminations. For MICRO FOOT analog switching products manufactured with tin/silver/copper (Sn/Ag/Cu) device terminations, the lead (Pb)-free "-E1" suffix is being used as a designator.

### **FEATURES**

- MICRO FOOT<sup>®</sup> Chip Scale Package (1.07 x 1.57 mm)
- Low Voltage Operation (1.8 V to 5.5 V)
- Low On-Resistance R<sub>DS(on)</sub>: 1.4 Ω
- Fast Switching t<sub>ON</sub>: 24 ns, t<sub>OFF</sub>: 9 ns
- Low Power Consumption
- TTL/CMOS Compatible

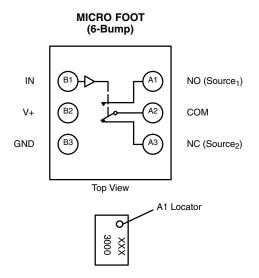
### **BENEFITS**

- **Reduced Power Consumption**
- Simple Logic Interface
- High Accuracy
- Reduce Board Space

### **APPLICATIONS**

- Cellular Phones
- Communication Systems
- Portable Test Equipment
- **Battery Operated Systems**
- **PCM Cards**
- PDA

### **FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION**



Device	Marking:	3000
xxx = Date/L	of Traceal	nility Code

TRUTH TABL	E	
Logic	NC	NO
0	ON	OFF
1	OFF	ON

ORDERING	INFORMATION	
Temp Range	Package	Part Number
- 40 °C to 85 °C	MICRO FOOT: 6-Bump 3 x 2, 0.5 mm Pitch 165 μm nom. bump height (Eutectic, SnPb)	DG3000DB-T1
- 40 0 10 65 0	MICRO FOOT: 6-Bump 3 x 2, 0.5 mm pitch, 238 μm nom. bump height (Lead (Pb)-free, Sn/Ag/Cu)	DG3000DB-T1- E1

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<sup>\*</sup> Pb containing terminations are not RoHS compliant, exemptions may apply.

# **DG3000**

# Vishay Siliconix



ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C, unless otherwise noted)					
Parameter		Limit	Unit		
Referenced V+ to GND		- 0.3 to + 6 V			
IN, COM, NC, NO <sup>a</sup>		- 0.3 V to (V+ + 0.3 V)	V		
Continuous Current (Any Terminal)	erminal) ± 50				
Peak Current (Pulsed at 1 ms, 10 % du	± 200	– mA			
Storage Temperature (D Suffix)	- 65 to 150	°C			
Package Reflow Conditions <sup>b</sup>					
VPR (Eutectic) 215					
IR/Convection (Eutectic)	220	°C			
IR/Convection (Lead (Pb)-free)	250				
Power Dissipation (Packages) <sup>c</sup>	6-Bump, 3 x 2 MICRO FOOT <sup>d</sup>	250	mW		

### Notes:

- a. Signals on NC, NO, or COM or IN exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings. b. Refer to IPC/JEDEC (J-STD-020A). No hand/manual solder rework recommended. c. All bumps soldered to PC Board.

- d. Derate 3.1 mW/°C above 70 °C.

SPECIFICATIONS (V-	+ = 2 V)						
		Test Conditions Otherwise Unless Specified		<b>Limits</b> - 40 °C to 85 °C			
Parameter	Symbol	$V+ = 2 V$ , $\pm 10 \%$ , $V_{IN} = 0.4 V$ or 1.6 $V^e$	Temp.a	Min.b	Typ. <sup>c</sup>	Max.b	Unit
Analog Switch	·			I.	I.	l .	
Analog Signal Range <sup>d</sup>	$V_{NO}, V_{NC} V_{COM}$		Full	0		V+	٧
On-Resistance	r <sub>ON</sub>	V+ = 1.8 V, V <sub>COM</sub> = 1 V, I <sub>NO</sub> , I <sub>NC</sub> = 10 mA	Room Full <sup>d</sup>		17	20 22.5	Ω
r <sub>ON</sub> Flatness <sup>d</sup>	r <sub>ON</sub> Flatness	$V+ = 1.8 \text{ V}, V_{COM} = 0 \text{ to } V+, I_{NO}, I_{NC} = 10 \text{ mA}$	Room		14		22
Switch Off Leakage Current <sup>f</sup>	I <sub>NO(off)</sub> I <sub>NC(off)</sub>	V+ = 2.2 V	Room Full <sup>d</sup>	- 700 - 11		700 11	pA nA
Switch Off Leakage Current	I <sub>COM(off)</sub>	$V_{NO}$ , $V_{NC} = 0.5 \text{ V/1.5 V}$ , $V_{COM} = 1.5 \text{ V/0.5 V}$	Room Full <sup>d</sup>	- 700 - 11		700 11	pA nA
Channel-On Leakage Current <sup>f</sup>	I <sub>COM(on)</sub>	$V+ = 2.2 \text{ V}, V_{NO}, V_{NC} = V_{COM} = 0.5 \text{ V}/1.5 \text{ V}$	Room Full <sup>d</sup>	- 700 - 11		700 11	pA nA
Digital Control							
Input High Voltage	V <sub>INH</sub>		Full	1.6			V
Input Low Voltage	V <sub>INL</sub>		Full			0.4	V
Input Capacitance <sup>d</sup>	C <sub>in</sub>		Full		5		pF
Input Current <sup>d</sup>	I <sub>INL</sub> or I <sub>INH</sub>	$V_{IN} = 0$ or $V+$	Full	- 1		1	μΑ
Dynamic Characteristics							
Turn-On Time	t <sub>ON</sub>	V 22V 45VB 2000 0 0 05 75	Room Full <sup>d</sup>		61	76 79	
Turn-Off Time	t <sub>OFF</sub>	$V_{NO}$ or $V_{NC}$ = 1.5 V, $R_L$ = 300 $\Omega$ , $C_L$ = 35 pF Figures 1 and 2	Room Full <sup>d</sup>		17	33 36	ns
Break-Before-Make Time	t <sub>d</sub>		Room	1	45		
Charge Injection <sup>d</sup>	Q <sub>INJ</sub>	$C_L = 1 \text{ nF, } V_{GEN} = 0 \text{ V, } R_{GEN} = 0 \Omega, \text{ Figure 3}$	Room		2		рC
Off-Isolation <sup>d</sup>	OIRR	$R_1 = 50 \Omega$ , $C_1 = 5 pF$ , $f = 1 MHz$	Room		- 61		dB
Crosstalk <sup>d</sup>	X <sub>TALK</sub>	11 <u>L</u> = 30 22, O <sub>L</sub> = 3 ρ1, 1 = 1 1911 12	Room		- 67		ub
NO, NC Off Capacitance <sup>d</sup>	C <sub>NO(off)</sub> C <sub>NC(off)</sub>	V <sub>IN</sub> = 0 or V+, f = 1 MHz	Room		31		pF
Channel-On Capacitance <sup>d</sup>	C <sub>ON</sub>		Room		98		
Power Supply							
Power Supply Range	V+			1.8		2.2	V
Power Supply Current <sup>d</sup>	l+	$V_{IN} = 0$ or $V+$			0.1	1	μΑ
Power Consumption	P <sub>C</sub>	V IIV — 0 01 V I				2.2	μW





SPECIFICATIONS (V-	- = 3 V)		T		1 1			
		Test Conditions Otherwise Unless Specified		Limits - 40 °C to 85 °C			Unit	
Parameter	Symbol	$V+ = 3 V, \pm 10 \%, V_{IN} = 0.4 V \text{ or } 2 V^{e}$	Temp.a	Min.b	Typ. <sup>c</sup>	/p. <sup>c</sup> Max. <sup>b</sup>		
Analog Switch								
Analog Signal Range <sup>d</sup>	$V_{NO}, V_{NC} V_{COM}$	F		0		V+	V	
On-Resistance <sup>d</sup>	R <sub>ON</sub>	$V+ = 2.7 \text{ V}, V_{COM} = 1.5 \text{ V}, I_{NO}, I_{NC} = 10 \text{ mA}$	Room Full		3.3 3.4	4.1 4.2	Ω	
R <sub>ON</sub> Flatness <sup>d</sup>	R <sub>ON</sub> Flatness	$V+ = 2.7 \text{ V}, V_{COM} = 0 \text{ to } V+, I_{NO}, I_{NC} = 10 \text{ mA}$			1.3		22	
Switch Off Leakage Current <sup>f</sup>	I <sub>NO(off)</sub> I <sub>NC(off)</sub>	V+ = 3.3 V	Room Full	- 800 - 13		800 13	pA nA	
Switch Off Leakage Guiletit	I <sub>COM(off)</sub>	V <sub>NO</sub> , V <sub>NC</sub> = 1 V/3 V, V <sub>COM</sub> = 3 V/1 V	Room Full	- 800 - 13		800 13	pA nA	
Channel-On Leakage Current <sup>f</sup>	I <sub>COM(on)</sub>	$V+ = 3.3 \text{ V}, V_{NO}, V_{NC} = V_{COM} = 1 \text{ V/3 V}$	Room Full	- 800 - 13		800 13	pA nA	
Digital Control								
Input High Voltage	V <sub>INH</sub>			2			V	
Input Low Voltage	$V_{INL}$		Full			0.4	v	
Input Capacitance <sup>d</sup>	C <sub>in</sub>		Full		5		pF	
Input Current <sup>d</sup>	I <sub>INL</sub> or I <sub>INH</sub>	$V_{IN} = 0$ or V+	Full	- 1		1	μΑ	
Dynamic Characteristics								
Turn-On Time <sup>d</sup>	t <sub>ON</sub>	$V_{NO}$ or $V_{NC}$ = 2 V, $R_L$ = 300 Ω, $C_L$ = 35 pF	Room Full		34	49 52		
Turn-Off Time <sup>d</sup>	t <sub>OFF</sub>	Figures 1 and 2	Room Full		12	30 33	ns	
Break-Before-Make Time <sup>d</sup>	t <sub>d</sub>		Room	1	23			
Charge Injection <sup>d</sup>	Q <sub>INJ</sub>	$C_L = 1 \text{ nF, } V_{GEN} = 0 \text{ V, } R_{GEN} = 0 \Omega, \text{ Figure 3}$	Room		4		рC	
Off-Isolation <sup>d</sup>	OIRR	$R_1 = 50 \Omega$ , $C_1 = 5 pF$ , $f = 1 MHz$	Room		- 61		٩D	
Crosstalk <sup>d</sup>	X <sub>TALK</sub>	$n_L = 50 \text{ sz}, G_L = 5 \text{ pr}, I = 1 \text{ Winz}$	Room		- 67		dB	
NO, NC Off Capacitance <sup>d</sup>	$C_{NO(off)} \ C_{NC(off)}$	V <sub>IN</sub> = 0 or V+, f = 1 MHz	Room		31		pF	
Channel-On Capacitance <sup>d</sup>	C <sub>ON</sub>		Room	om 47				
Power Supply			•					
Power Supply Range	V+			2.7		3.3	V	
Power Supply Current <sup>d</sup>	I+	V <sub>IN</sub> = 0 or V+	V = 0 or V.		0.1	1	μΑ	
Power Consumption	P <sub>C</sub>	V IN = 0.01 V+				3.3	μW	

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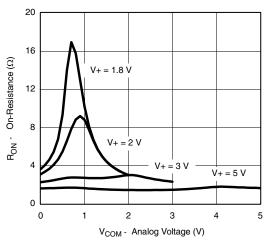
SPECIFICATIONS (V	/+ = 5 V)							
		Test Conditions Otherwise Unless Specified		- 40	<b>Limits</b> - 40 °C to 85 °C		Unit	
Parameter	Symbol	$V+ = 5 V$ , $\pm 10 \%$ , $V_{IN} = 0.8 V$ or 2.4 $V^e$	Temp.a	Min.b	Typ. <sup>c</sup>	Max.b		
Analog Switch								
Analog Signal Range <sup>d</sup>	$V_{NO}, V_{NC} \ V_{COM}$		Full	0		V+	V	
On- Resistance	R <sub>ON</sub>	$V+ = 4.5 \text{ V}, V_{COM} = 3 \text{ V}, I_{NO}, I_{NC} = 10 \text{ mA}$	Room Full		1.4 1.6	2.3 2.8	Ω	
R <sub>ON</sub> Flatness <sup>d</sup>	R <sub>ON</sub> Flatness	$V+ = 4.5 \text{ V}, V_{COM} = 0 \text{ to } V+, I_{NO}, I_{NC} = 10 \text{ mA}$	Room		0.5		52	
Switch Off Leakage Current	$I_{NO(off)}$ $I_{NC(off)}$	V+ = 5.5 V	Room Full	- 1.2 - 21		1.2 21		
Switch On Leakage Ourient	I <sub>COM(off)</sub>	$V_{NO}$ , $V_{NC} = 1 \text{ V}/4.5 \text{ V}$ , $V_{COM} = 4.5 \text{ V}/1 \text{ V}$	Room Full	- 1.2 - 21		1.2 21	nA	
Channel-On Leakage Current	I <sub>COM(on)</sub>	V+ = 5.5 V, V+ = 5.5 V $V_{NO}, V_{NC} = V_{COM} = 1 V/4.5 V$	Room Full	- 1.2 - 21		1.2 21		
Digital Control			1		•		L	
Input High Voltage	$V_{INH}$		Full	2.4			V	
Input Low Voltage	V <sub>INL</sub>		Full			0.8	V	
Input Capacitance	C <sub>in</sub>		Full		5		pF	
Input Current	I <sub>INL</sub> or I <sub>INH</sub>	$V_{IN} = 0$ or V+	Full	- 1		1	μΑ	
Dynamic Characteristics								
Turn-On Time <sup>d</sup>	t <sub>ON</sub>	$V_{NO}$ or $V_{NC}$ = 3 V, $R_L$ = 300 $\Omega$ , $C_L$ = 35 pF	Room Full		24	36 39		
Turn-Off Time <sup>d</sup>	t <sub>OFF</sub>	Figures 1 and 2	Room Full		9	22 25	ns	
Break-Before-Make Time <sup>d</sup>	t <sub>d</sub>		Room	1	15			
Charge Injection <sup>d</sup>	$Q_{INJ}$	$C_L$ = 1 nF, $V_{GEN}$ = 0 V, $R_{GEN}$ = 0 $\Omega$ , Figure 3	Room		38		рС	
Off-Isolation <sup>d</sup>	OIRR	$R_1 = 50 \Omega$ , $C_1 = 5 pF$ , $f = 1 MHz$	Room		- 61		٦D	
Crosstalk <sup>d</sup>	X <sub>TALK</sub>	$n_L = 30.52$ , $O_L = 3.61$ , $T = 1.101112$	Room		- 67		dB	
Source-Off Capacitance <sup>d</sup>	C <sub>NO(off)</sub> C <sub>NC(off)</sub>	V <sub>IN</sub> = 0 or V+, f = 1 MHz	Room		30		рF	
Channel-On Capacitance <sup>d</sup>	C <sub>ON</sub>		Room		96			
Power Supply								
Power Supply Range	V+			4.5		5.5	V	
Power Supply Current	l+	V <sub>IN</sub> = 0 or V+			0.1	1	μΑ	
Power Consumption	$P_{C}$	VIN - O OI VT				5.5	μW	

- a. Room = 25  $^{\circ}$ C, full = as determined by the operating suffix.
- b. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- c. Typical values are for design aid only, not guaranteed nor subject to production testing.
- d. Guarantee by design, nor subjected to production test.
- e. V<sub>IN</sub> = input voltage to perform proper function.
- f. Guaranteed by 5 V leakage testing, not production tested.

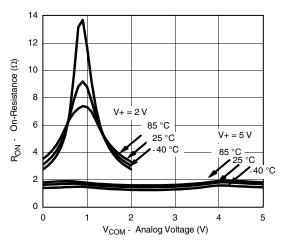
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



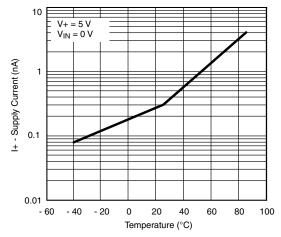
### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



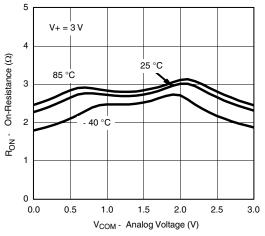
 $R_{ON}$  vs.  $V_{COM}$  and Supply Voltage



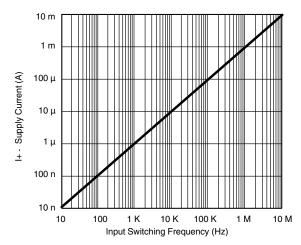
R<sub>ON</sub> vs. Analog Voltage and Temperature



Supply Current vs. Temperature



R<sub>ON</sub> vs. Analog Voltage and Temperature

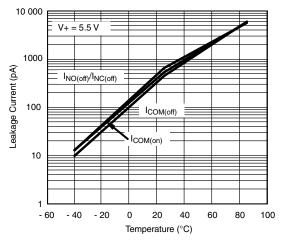


**Supply Current vs. Input Switching Frequency** 

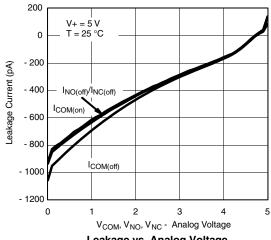
# **DG3000**

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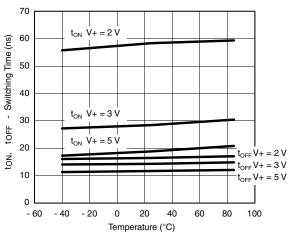
### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



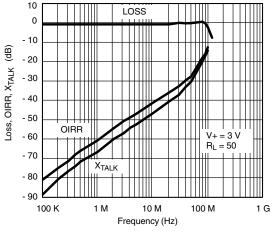
Leakage Current vs. Temperature



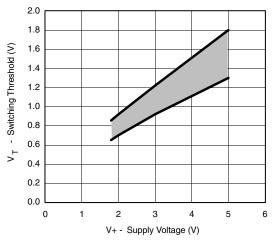
Leakage vs. Analog Voltage



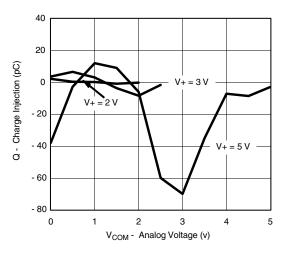
Switching Time vs. Temperature and Supply Voltage



Insertion Loss, Off-Isolation, Crosstalk vs. Frequency



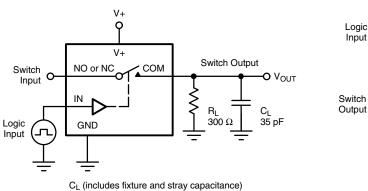
Switching Threshold vs. Supply Voltage



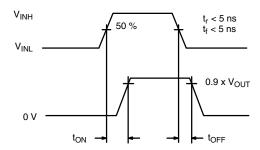
Charge Injection vs. Analog Voltage



### **TEST CIRCUITS**



$$V_{OUT} = V_{COM} \left( \frac{R_L}{R_L + R_{ON}} \right)$$



Logic "1" = Switch On Logic input waveforms inverted for switches that have the opposite logic sense.

Figure 1. Switching Time

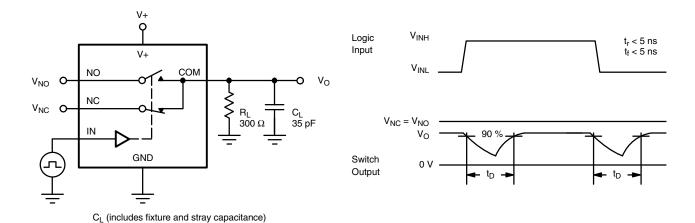
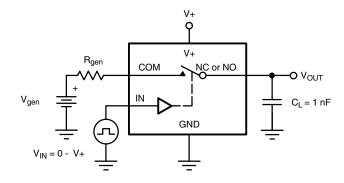
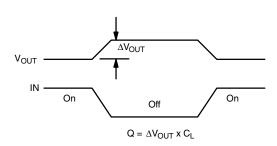


Figure 2. Break-Before-Make Interval





IN depends on switch configuration: input polarity determined by sense of switch.

Figure 3. Charge Injection

## **TEST CIRCUITS**



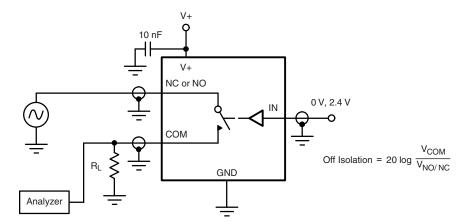


Figure 4. Off-Isolation

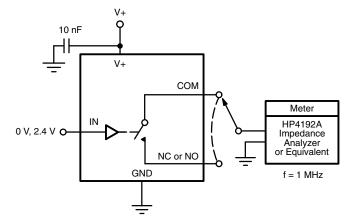
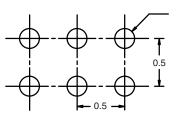


Figure 5. Channel Off/On Capacitance



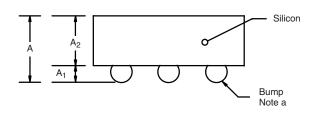
### **PACKAGE OUTLINE**

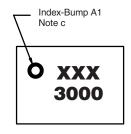
### MICRO FOOT: 6-BUMP (3 x 2, 0.5 mm PITCH)



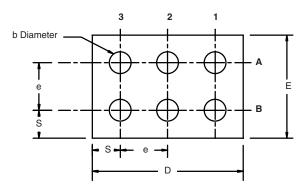
6 x Ø 0.150 ~ 0.229 Solder Mask Ø ~ Pad Dia. + 0.1

Recommended Land Pattern





Top Side (Die Back)



Notes (Unless Otherwise Specified):

- a. Bump is Eutectic 63/57 Sn/Pb or Lead (Pb)-free Sn/Ag/Cu.
- b. Non-solder mask defined copper landing pad.
- c. Laser Mark on silicon die back; no coating. Shown is not actual marking; sample only.

EUTECTIC (Sn/Pb)					
	Millim	eters <sup>a</sup>	Inc	hes	
Dim.	Min.	Max.	Min. Max		
Α	0.615	0.715	0.0242	0.0281	
A <sub>1</sub>	0.140	0.190	0.0055	0.0075	
A <sub>2</sub>	0.470	0.495	0.0185	0.0195	
b	0.180	0.250	0.0071	0.0098	
D	1.555	1.585	0.0612	0.0624	
E	1.055	1.085	0.0415	0.0427	
е	0.5 BASIC		0.0197 BASIC		
S	0.278	0.293	0.0109 0.011		

Notes:	
INULES.	

a. Use millimeters as the primary measurement.

LEAD (I	Pb)-FREE	(Sn/Ag/C	u)			
	Millim	eters <sup>a</sup>	Inches			
Dim.	Min.	Max.	Min. Max.			
Α	0.688	0.753	0.0271	0.0296		
A <sub>1</sub>	0.218	0.258	0.0086	0.0102		
A <sub>2</sub>	0.470	0.495	0.0185 0.019			
b	0.306	0.346	0.0120	0.0136		
D	1.555	1.585	0.0612	0.0624		
E	1.055	1.085	0.0415 0.042			
е	0.5 B	ASIC	0.0197 BASIC			
S	0.278	0.293	0.0109	0.0115		

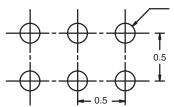
a. Use millimeters as the primary measurement.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?71742.

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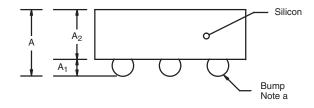


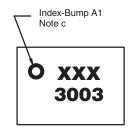
### MICRO FOOT: 6-BUMP (3 mm x 2 mm, 0.5 mm PITCH, 165 µm BUMP HEIGHT)



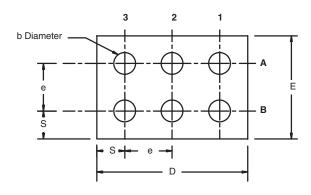
6 x Ø 0.150 □ 0.229 Note b Solder Mask Ø ☐ Pad Dia. + 0.1

Recommended Land Pattern





Top Side (Die Back)



### Notes

(unless otherwise specified)

- a. Bump is Eutectic 63/57 Sn/Pb or lead (Pb)-free Sn/Ag/Cu.
- b. Non-solder mask defined copper landing pad.
- c. Laser mark on silicon die back; no coating. Shown is not actual marking; sample only.

EUTECI	TIC (Sn/Pb)	)			
DIM.	MILLIM	ETERS <sup>a</sup>	INC	HES	
DIW.	MIN.	MAX.	MIN.	MAX.	
Α	0.610	0.685	0.0240	0.0270	
A <sub>1</sub>	0.140	0.190	0.0055	0.0075	
A <sub>2</sub>	0.470	0.495	0.0185	0.0195	
b	0.180	0.250	0.0071	0.0098	
D	1.490	1.515	0.0587	0.0596	
Е	0.990	1.015	0.0390	0.0400	
е	0.5 B	ASIC	0.0197 BASIC		
S	0.245	0.258	0.0096 0.010		

a. Use millimeters as the primary measurement.

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LEAD (Pb)-FREE (Sn/Ag/Cu)							
DIM.	MILLIMETERSa		INCHES				
	MIN.	MAX.	MIN.	MAX.			
Α	0.688	0.753	0.0271	0.0296			
A <sub>1</sub>	0.218	0.258	0.0086	0.0102			
A <sub>2</sub>	0.470	0.495	0.0185	0.0195			
b	0.306	0.346	0.0120	0.0136			
D	1.490	1.515	0.0587	0.0596			
Е	0.990	1.015	0.0390	0.0400			
е	0.5 BASIC		0.0197 BASIC				
S	0.245	0.258	0.0096	0.0101			

a. Use millimeters as the primary measurement.

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# PCB Design and Assembly Guidelines For MICRO FOOT® Products

Johnson Zhao

### INTRODUCTION

Vishay Siliconix's MICRO FOOT product family is based on a wafer-level chip-scale packaging (WL-CSP) technology that implements a solder bump process to eliminate the need for an outer package to encase the silicon die. MICRO FOOT products include power MOSFETs, analog switches, and power ICs.

For battery powered compact devices, this new packaging technology reduces board space requirements, improves thermal performance, and mitigates the parasitic effect typical of leaded packaged products. For example, the 6-bump MICRO FOOT Si8902EDB common drain power MOSFET, which measures just 1.6 mm x 2.4 mm, achieves the same performance as TSSOP-8 devices in a footprint that is 80% smaller and with a 50% lower height profile (Figure 1). A MICRO FOOT analog switch, the 6-bump DG3000DB, offers low charge injection and 1.4 W on-resistance in a footprint measuring just 1.08 mm x 1.58 mm (Figure 2).

Vishay Siliconix MICRO FOOT products can be handled with the same process techniques used for high-volume assembly of packaged surface-mount devices. With proper attention to PCB and stencil design, the device will achieve reliable performance without underfill. The advantage of the device's small footprint and short thermal path make it an ideal option for space-constrained applications in portable devices such as battery packs, PDAs, cellular phones, and notebook computers.

This application note discusses the mechanical design and reliability of MICRO FOOT, and then provides guidelines for board layout, the assembly process, and the PCB rework process.

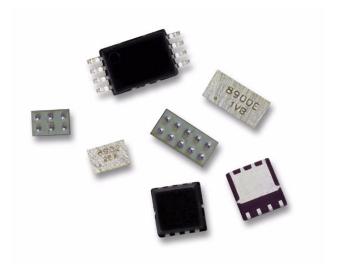


FIGURE 1. 3D View of MICRO FOOT Products Si8902DB and Si8900EDB

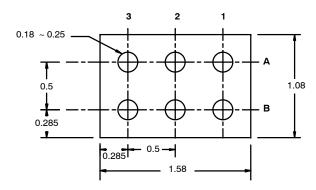


FIGURE 2. Outline of MICRO FOOT CSP & Analog Switch DG3000DB



TABLE 1  Main Parameters of Solder Bumps in MICRO FOOT Designs						
MICRO FOOT CSP	Bump Material	Bump Pitch*	Bump Diameter*	Bump Height*		
MICRO FOOT CSP MOSFET	5 0.11	0.8	0.37-0.41	0.26-0.29		
MICRO FOOT CSP Analog Switch	Eutectic Solder: 63Sm/37Pb	0.5	0.18-0.25	0.14-0.19		
MICRO FOOT UCSP Analog Switch		0.5	0.32-0.34	0.21-0.24		

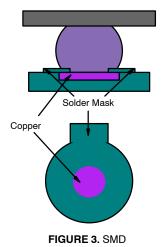
<sup>\*</sup> All measurements in millimeters

### MICRO FOOT'S DESIGN AND RELIABILITY

As a mechanical, electrical, and thermal connection between the device and PCB, the solder bumps of MICRO FOOT products are mounted on the top active surface of the die. Table 1 shows the main parameters for solder bumps used in MICRO FOOT products. A silicon nitride passivation layer is applied to the active area as the last masking process in fabrication, ensuring that the device passes the pressure pot test. A green laser is used to mark the backside of the die without damaging it. Reliability results for MICRO FOOT products mounted on a FR-4 board without underfill are shown in Table 2.

TABLE 2 MICRO FOOT Reliability Results			
Test Condition C: −65° to 150°C	>500 Cycles		
Test condition B: −40° to 125°C	>1000 Cycles		
121°C @ 15PSI 100% Humidity Test	96 Hours		

The main failure mechanism associated with wafer-level chip-scale packaging is fatigue of the solder joint. The results shown in Table 2 demonstrate that a high level of reliability can be achieved with proper board design and assembly techniques.



### **BOARD LAYOUT GUIDELINES**

**Board materials**. Vishay Siliconix MICRO FOOT products are designed to be reliable on most board types, including organic boards such as FR-4 or polyamide boards. The package qualification information is based on the test on 0.5-oz. FR-4 and polyamide boards with NSMD pad design.

**Land patterns.** Two types of land patterns are used for surface-mount packages. Solder mask defined (SMD) pads have a solder mask opening smaller than the metal pad (Figure 3), whereas on-solder mask defined (NSMD) pads have a metal pad smaller than the solder-mask opening (Figure 4).

NSMD is recommended for copper etch processes, since it provides a higher level of control compared to SMD etch processes. A small-size NSMD pad definition provides more area (both lateral and vertical) for soldering and more room for escape routing on the PCB. By contrast, SMD pad definition introduces a stress -concentration point near the solder mask on the PCB side that may result in solder joint cracking under extreme fatigue conditions.

Copper pads should be finished with an organic solderability preservative (OSP) coating. For electroplated nickel-immersion gold finish pads, the gold thickness must be less than 0.5  $\mu$ m to avoid solder joint embrittlement.

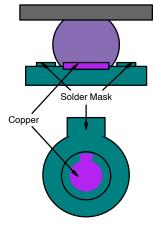


FIGURE 4. NSMD

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**Board pad design.** The landing-pad size for MICRO FOOT products is determined by the bump pitch as shown in Table 3. The pad pattern is circular to ensure a symmetric, barrel-shaped solder bump.

TABLE 3 Dimensions of Copper Pad and Solder Mask Opening in PCB and Stencil Aperture						
Pitch	Copper Pad	Solder Mask Opening	Stencil Aperture			
0.80 mm	0.30 ± 0.01 mm	0.41 ± 0.01 mm	0.33 ± 0.01 mm in ciircle aperture			
0.50 mm	0.17 ± 0.01 mm	0.27 ± 0.01 mm	$0.30\pm0.01$ mm in square aperture			

### ASSEMBLY PROCESS

MICRO FOOT products' surface-mount-assembly operations include solder paste printing, component placement, and solder reflow as shown in the process flow chart (Figure 5).



FIGURE 5. SMT Assembly Process Flow

**Stencil design**. Stencil design is the key to ensuring maximum solder paste deposition without compromising the assembly yield from solder joint defects (such as bridging and extraneous solder spheres). The stencil aperture is dependent on the copper pad size, the solder mask opening, and the quantity of solder paste.

In MICRO FOOT products, the stencil is 0.125-mm (5-mils) thick. The recommended apertures are shown in Table 3 and are fabricated by laser cut.

**Solder-paste printing.** The solder-paste printing process involves transferring solder paste through pre-defined apertures via application of pressure.

In MICRO FOOT products, the solder paste used is UP78 No-clean eutectic 63 Sn/37Pb type3 or finer solder paste.

**Chip pick-and-placement.** MICRO FOOT products can be picked and placed with standard pick-and-place equipment. The recommended pick-and-place force is 150 g. Though the part will self-center during solder reflow, the maximum placement offset is 0.02 mm.

**Reflow Process.** MICRO FOOT products can be assembled using standard SMT reflow processes. Similar to any other package, the thermal profile at specific board locations must be determined. Nitrogen purge is recommended during reflow operation. Figure 6 shows a typical reflow profile.

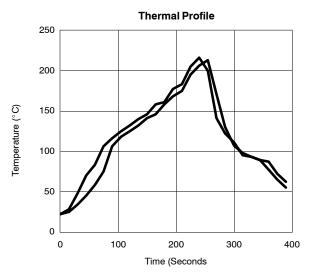


FIGURE 6. Reflow Profile

### **PCB REWORK**

To replace MICRO FOOT products on PCB, the rework procedure is much like the rework process for a standard BGA or CSP, as long as the rework process duplicates the original reflow profile. The key steps are as follows:

- Remove the MICRO FOOT device using a convection nozzle to create localized heating similar to the original reflow profile. Preheat from the bottom.
- Once the nozzle temperature is +190°C, use tweezers to remove the part to be replaced.
- Resurface the pads using a temperature-controlled soldering iron.
- Apply gel flux to the pad.
- Use a vacuum needle pick-up tip to pick up the replacement part, and use a placement jig to placed it accurately.
- Reflow the part using the same convection nozzle, and preheat from the bottom, matching the original reflow profile.



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